TOSHIBA Photo-interrupter Infrared LED+Phototransistor

TLP842

Still Camera and Digital Still Camera

Video Camera

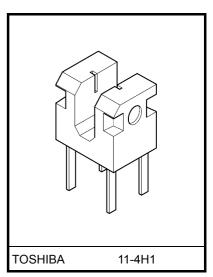
Floppy Disk Drive

Small-sized Personal OA Equipment

The TLP842 is photointerrupter which consists of a GaAs infrared LED and an Si phototransistor.

It is an ultra compact package and has a wide gap width. More it has a narrow slit and a high resolution.

- Ultra compact package: 3.5×2.6×2.9mm
- Gap width: 1.2 mm
- High resolution: Slit width = 0.15 mm
- High current transfer ratio: IC/IF = 3% (min)
- Material of the package: Polybutylene terephthalate (UL94V-0)
- Lead-free product

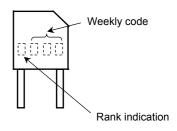


Weight: 0.035 g (typ.)

Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit	
ΠED	Forward current	lF	30	mA	
	Forward current derating (Ta>25°C)	ΔI _F /°C	-0.33	mA/°C	
	Reverse voltage	V_{R}	5	V	
Detector	Collector-emitter voltage	V _{CEO}	35	V	
	Emitter-collector voltage	V _{ECO}	5	V	
	Collector power dissipation	PC	75	mW	
	Collector power dissipation derating (Ta>25°C)	ΔP _C /°C	-1	mW/°C	
	Collector current	Ic	50	mA	
Operating temperature range		T _{opr}	-30 to 85	°C	
Storage temperature range		T _{stg}	-40 to 100	°C	
Sold	ering temperature (5s) (Note 1)	T _{sol}	260	°C	

Marking (Note 2)

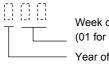


Note 1: At least 1mm from body

Note 2: It is composed of the Arabic numerals four digits, one digit from the left shows Rank indication and the rest three digits show Weekly code.

※Rank indication Without a mark: None R: R rank device

Weekly code: (Three digits)



Week of manufacture

(01 for first week of year, continues up to 52 or 53)

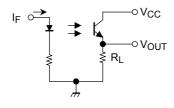
Year of manufacture

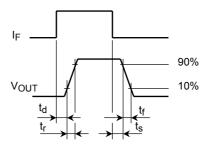
(One low-order digits of calendar year)

Optical and Electrical Characteristics (Ta = 25°C)

Characteristics		Symbol	Test conditions		Min	Тур.	Max	Unit
LED	Forward voltage	V_{F}	I _F = 10 mA		1.00	1.23	1.40	V
	Reverse current	I _R	V _R = 5 V		_	_	10	μΑ
	Peak emission wavelength	λ _P	I _F = 10 mA		_	940	_	nm
Detector	Dark current	ID (ICEO)	V _{CE} = 24 V, I _F = 0		_	_	0.1	μΑ
	Peak sensitivity wavelength	λ _P	_		_	820	_	nm
Coupled	Current transfer ratio	1-/1-	V _{CE} = 2 V	TLP842	3	_	24	%
		I _C /I _F	I _F = 5 mA	TLP842 (R)	4	_	20	
	Collector-emitter saturation voltage	V _{CE} (sat)	$I_F = 10 \text{ mA}, I_C = 0.25 \text{ mA}$		_	0.1	0.4	V
	Rise time	t _r	$V_{CE} = 5 \text{ V}, I_C = 1 \text{ mA}, R_L = 1 \text{ k}\Omega$		_	15	50	6
	Fall time	t _f		_	15	50	μS	

Note 3: Switching time measurement circuit and waveform





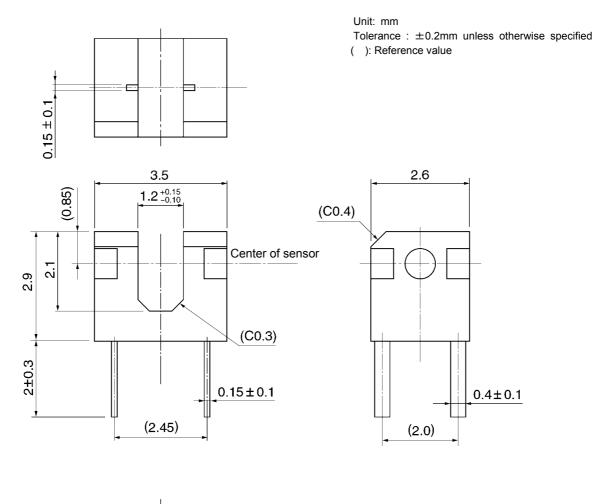
Precautions

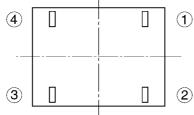
- When removing flux with chemicals after soldering, clean only the leads on the soldering side; do not dip the whole package for cleaning.
 - Chemicals remaining on an LED or photo transistor light emitter or receiver, if any, would have a bad influence to the optical characteristics and it may severely lower the conversion efficiency.
- Care must be taken in relation to the environment in which the device is to be installed. Oil or chemicals may cause the package to melt or crack.
- The device should be mounted on an unwarped surface.
- Conversion efficiency falls over time due to the current which flows in the infrared LED. When designing a circuit, take into account this change in conversion efficiency over time. The ratio of fluctuation in conversion efficiency to fluctuation in infrared LED optical output is 1:1.

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$$\frac{I_{C}/I_{F}(t)}{I_{C}/I_{F}(0)} = \frac{P_{O}(t)}{P_{O}(0)}$$

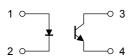
Package Dimensions: TOSHIBA 11-4H1





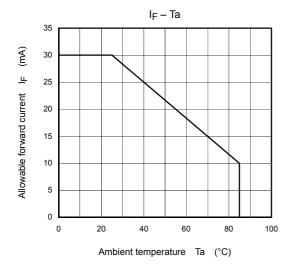
Weight: 0.035g (typ.)

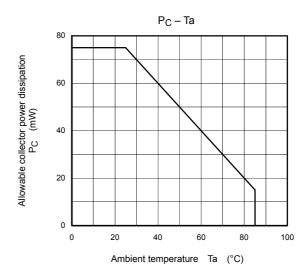
Pin Connection

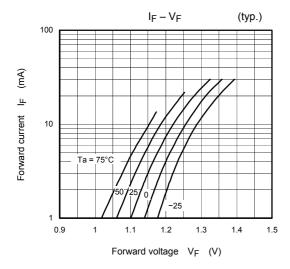


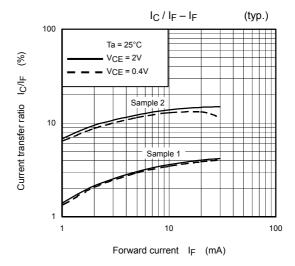
- 1: Anode
- 2: Cathode
- 3: Collector
- 4: Emitter

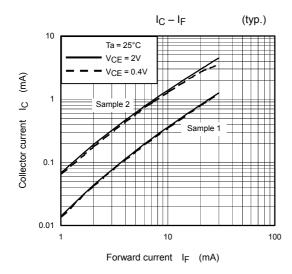
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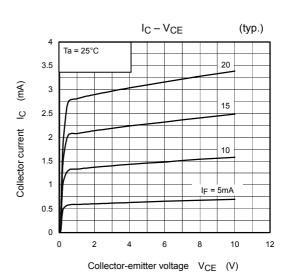


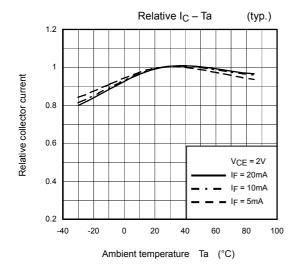


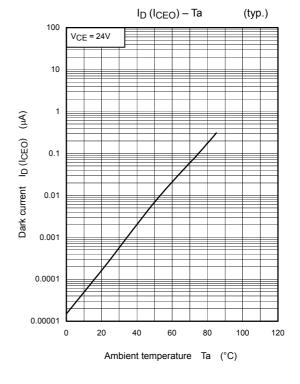


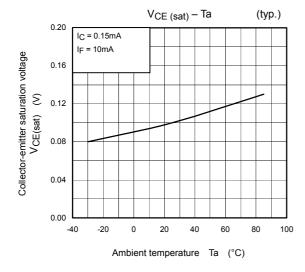


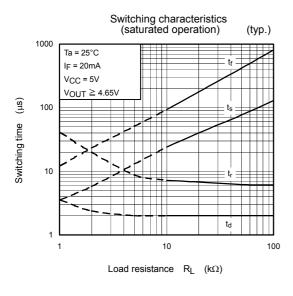


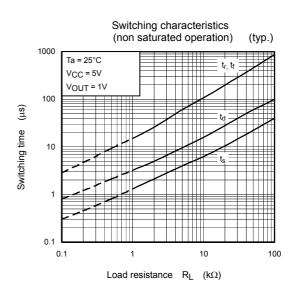




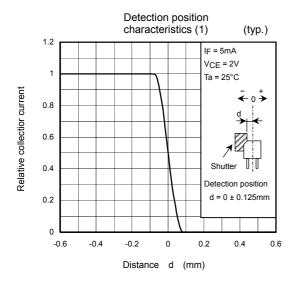


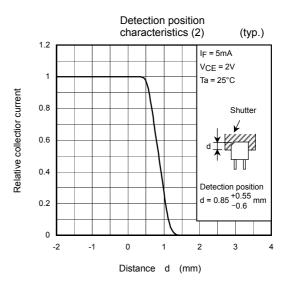






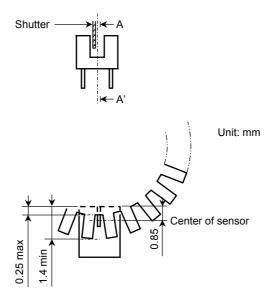
5





Relative Positioning of Shutter and Device

For normal operation, position the shutter and the device as shown in the figure below. By considering the device's detection direction characteristic and switching time, determine the shutter slit width and pitch.



Cross section between A and A'

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